

# **FGW15N120VD**

**Discrete IGBT** 

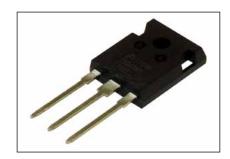
# Discrete IGBT (High-Speed V series) 1200V / 15A

#### ■ Features

Low power loss Low switching surge and noise High reliability, high ruggedness (RBSOA, SCSOA etc.)

#### Applications

Inverter for Motor drive AC and DC Servo drive amplifier Uninterruptible power supply

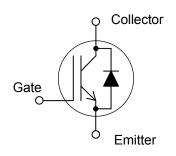


# ■ Maximum Ratings and Characteristics

## ● Absolute Maximum Ratings (at T<sub>c</sub>=25°C unless otherwise specified)

Items	Symbols	Characteristics	Units	Remarks
Collector-Emitter voltage	Vces	1200	V	
Gate-Emitter voltage	V <sub>GES</sub>	±20	V	
DC Collector Current	Ic@25	28	Α	Tc=25°C, Tj=150°C
	Ic@100	15	Α	Tc=100°C, Tj=150°C
Pulsed Collector Current	I <sub>CP</sub>	30	Α	Note *1
Turn-Off Safe Operating Area	-	30	Α	Vce≤1200V, Tj≤175°C
Diode Forward Current	I <sub>F@25</sub>	26	Α	
	IF@100	15	Α	
Diode Pulsed Current	I <sub>FP</sub>	30	Α	Note *1
Short Circuit Withstand Time	tsc	10	μs	Vcc≤640V, VgE=15V Tj≤150°C
IGBT Max. Power Dissipation	P <sub>D_IGBT</sub>	155	W	Tc=25°C
FWD Max. Power Dissipation	P <sub>D_FWD</sub>	95	۷V	Tc=25°C
<b>Operating Junction Temperature</b>	T <sub>j</sub>	-40~+175	ç	
Storage Temperature	T <sub>stg</sub>	-55~+175	°C	

**■** Equivalent circuit



Note \*1 : Pulse width limited by Tjmax.

#### ● Electrical characteristics (at T<sub>i</sub>= 25°C unless otherwise specified)

Itama	Symbols	Conditions	Ch	Characteristics					
Items	Symbols	Conditions	min.	typ.	max.	Unit			
Collector-Emitter Breakdown Voltage	V <sub>(BR)CES</sub>	$I_{C} = 50 \mu A, V_{GE} = 0 V$	1200	-	-	V			
ero Gate Voltage Collector Current Ices	Ices	$V_{CE} = 1200V, V_{GE} = 0V$ $T_1 = 25^{\circ}C$	-	-	250	μA			
	ICES	/ [1j=1/5°C	-	-	2	mA			
Gate-Emitter Leakage Current	Iges	$V_{CE} = 0V, V_{GE} = \pm 20V$	-	-	200	nA			
Gate-Emitter Threshold Voltage	V <sub>GE (th)</sub>	V <sub>CE</sub> = +20V, I <sub>C</sub> = 15mA	6.0	6.5	7.0	V			
Collector-Emitter Saturation Voltage	V <sub>CE</sub> (sat)	V <sub>GE</sub> = +15V. I <sub>C</sub> = 15A T <sub>1</sub> =25°C	-	1.85	2.4	V			
		I <sub>j</sub> =1/5°C	-	2.4	-	V			
Input Capacitance	Cies	V <sub>CE</sub> =25V	-	1015	-				
Output Capacitance	Coes	V <sub>GE</sub> =0V	-	58	-	pF			
Reverse Transfer Capacitance	Cres	f=1MHz	-	47	-				
Gate Charge		Vcc = 600V		150	-	nC			
	Q <sub>G</sub>	I <sub>c</sub> = 15A	-						
		V <sub>GE</sub> = 15V		07					
Turn-On Delay Time	t <sub>d(on)</sub>	T <sub>j</sub> = 25°C	-	27	-	ns			
Rise Time	t	Vcc = 600V	-	20	-				
Turn-Off Delay Time	t <sub>d(off)</sub>	I <sub>C</sub> = 15A V <sub>GF</sub> = 15V	-	180	-	4			
Fall Time	t <sub>r</sub>	$R_{G} = 100$	-	45	-	$\perp$			
Turn-On Energy	Eon		-	1.1	-				
Turn-Off Energy	Eoff	L = 500µH		0.0		mJ			
		Energy loss include "tail" and FWD reverse	-	8.0	-				
Turn-On Delay Time	t <sub>d(on)</sub>	recovery. T <sub>i</sub> = 175°C	_	28	-				
Rise Time	t <sub>r</sub>	V <sub>cc</sub> = 600V	<del>-</del>	22	-	ns			
Turn-Off Delay Time	t <sub>d(off)</sub>	Ic = 15A	-	245	-				
Fall Time	t <sub>f</sub>	V <sub>GE</sub> = 15V		75	-				
Turn-On Energy	Eon	$R_{G} = 10\Omega$		1.7	-				
Turn-On Energy	Lon	L = 500uH	<u> </u>	1.7	-				
Turn-Off Energy	Eoff	Energy loss include "tail" and FWD reverse	_	1.4	-	mJ			
	Lon	recovery.							
_		T-25°C	-	1.7	2.21	V			
Forward Voltage Drop	VF	I⊧=15A T;=175°C	-	1.8	-	V			
		Vcc=30V		56		ns			
Diode Reverse Recovery Time	t <sub>rr1</sub>	I <sub>F</sub> = 1.5A	-		73				
•		-di/dt=200A/µs							
Diode Reverse Recovery Time	t <sub>rr2</sub>	Vcc=600V	_	0.26	_				
	Lrr2	I <sub>=</sub> 15A		0.20		μs			
Diode Reverse Recovery Charge	Qrr	-di⊧/dt=200A/µs	_	0.85		μC			
Diode Neverse Recovery Charge	Q <sub>rr</sub>	T <sub>j</sub> =25°C	-	0.65	-	μΟ			

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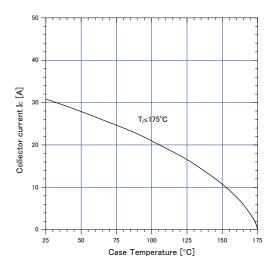
Items	Symbols Conditions		Characteristics			Unit
items	Syllibols	Conditions	min.	typ.	max.	Unit
Diode Reverse Recovery Time	t <sub>rr2</sub>	Vcc=600V I <sub>F</sub> =15A	-	0.65	-	μs
Diode Reverse Recovery Charge	Qrr	-di⊧/dt=200A/μs T⊫175°C	-	2.2	-	μC

# ● Thermal resistance

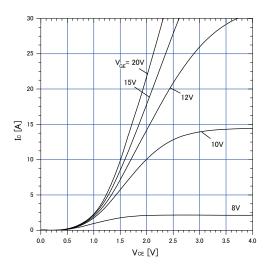
Items	Symbols		Unit		
items		min.	typ.	max.	Oilit
Thermal Resistance, Junction-Ambient	R <sub>th(j-a)</sub>	-	-	50	
Thermal Resistance, IGBT Junction to Case	R <sub>th(j-c)_IGBT</sub>	-	-	0.962	°C/W
Thermal Resistance, FWD Junction to Case	R <sub>th(j-c)_FWD</sub>	-	-	1.563	

## **■** Characteristics (Representative)

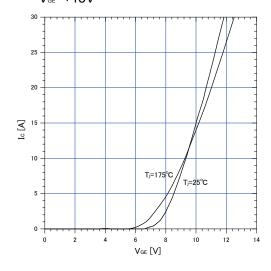
Graph.1 DC Collector Current vs  $T_c$   $V_{ce} \ge +15V$ ,  $T_i \le 175$ °C



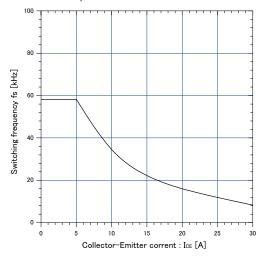
Graph.3 Typical Output Characteristics ( $V_{\text{CE}}$ - $I_{\text{C}}$ )  $T_{\text{J}}$ =25°C



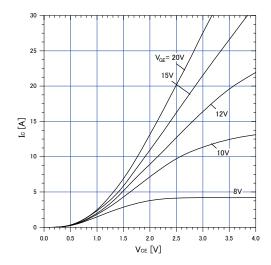
Graph.5 Typical Transfer Characteristics  $V_{\text{GE}}$ =+15V



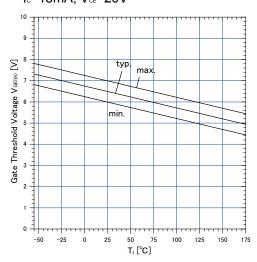
Graph.2 Collector Current vs. switching frequency  $V_{\text{og}}$ =+15V,  $T_{\text{o}}$ ≤175°C,  $V_{\text{co}}$ =600V, D=0.5,  $R_{\text{o}}$ =10 $\Omega$ ,  $T_{\text{o}}$ =100°C



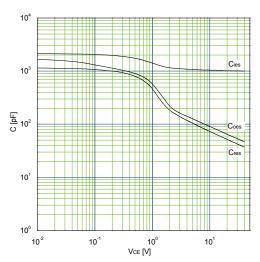
Graph.4 Typical Output Characteristics ( $V_{ce}$ - $I_c$ )  $T_j$ =175°C



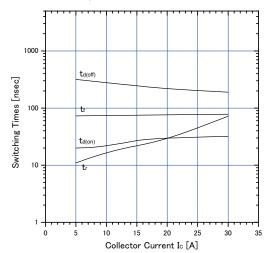
Graph.6
Gate Threshold Voltage vs. T<sub>i</sub>
I<sub>c</sub>=15mA, V<sub>cc</sub>=20V



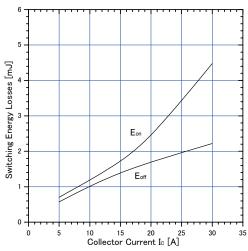
Graph.7 Typical Capacitance V<sub>□E</sub>=0V, f=1MHz, T<sub>i</sub>=25°C



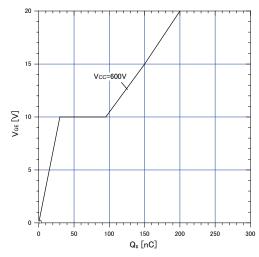
Graph.9 Typical switching time vs.  $I_c$  T<sub>j</sub>=175°C,  $V_{cc}$ =600V, L=500 $\mu$ H  $V_{ce}$ =15V, $R_c$ =10 $\Omega$ 



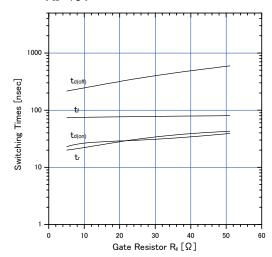
Graph.11 Typical switching losses vs.  $I_c$  T<sub>J</sub>=175°C,  $V_{cc}$ =600V, L=500 $\mu$ H  $V_{ce}$ =15V,  $R_c$ =10 $\Omega$ 



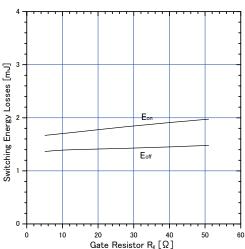
Graph.8 Typical Gate Charge V∞=600V, I₀=15A, T,=25°C



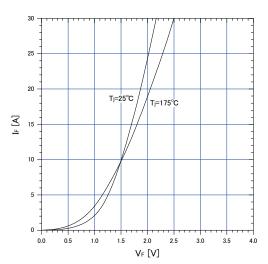
Graph.10 Typical switching time vs.  $R_s$   $T_s$ =175°C,  $V_{cc}$ =600V,  $I_c$ =15A, L=500 $\mu$ H  $V_{ce}$ =15V



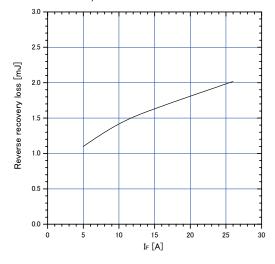
Graph.12 Typical switching losses vs.  $R_{\rm s}$  T<sub>i</sub>=175°C,  $V_{\rm cc}$ =600V,  $I_{\rm c}$ =15A, L=500 $\mu$ H  $V_{\rm se}$ =15V



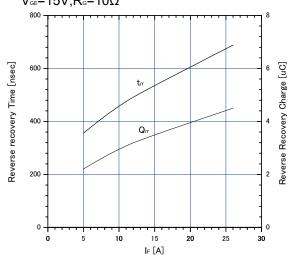
Graph.13 FWD Forward voltage drop (V<sub>F</sub>-I<sub>F</sub>)



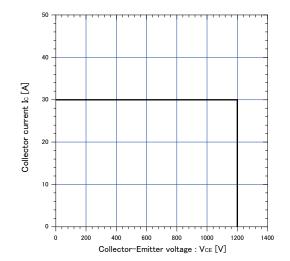
Graph.15 Typical reverse recovery loss vs. I<sub>F</sub> T<sub>i</sub>=175°C,V<sub>CC</sub>=600V,L=500 $\mu$ H V<sub>GE</sub>=15V,R<sub>G</sub>=10 $\Omega$ 



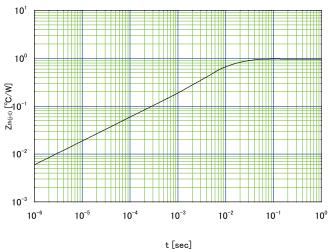
Graph.14 Typical reverse recovery characteristics vs.  $I_{\text{F}}$  T<sub>j</sub>=175°C, V<sub>cc</sub>=600V, L=500 $\mu$ H, V<sub>cE</sub>=15V,R<sub>c</sub>=10 $\Omega$ 



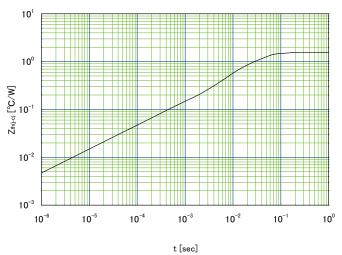
Graph.16 Reverse biased Safe Operating Area  $T_1 \le 175^{\circ}C$ ,  $V_{oe} = +15V/0V$ ,  $R_o = 10\Omega$ 



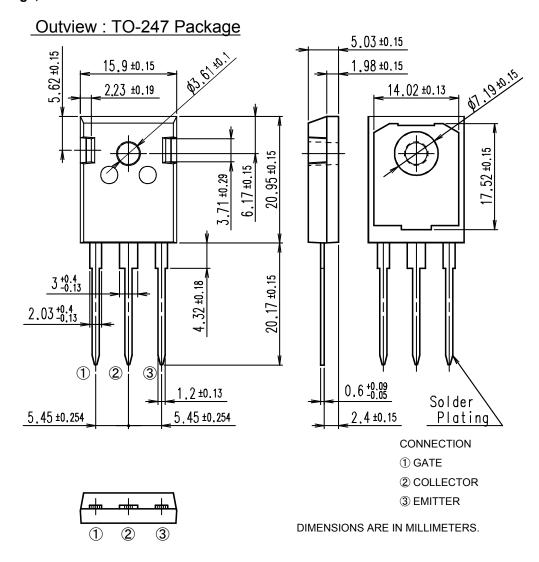
Graph.17
Transient thermal resistance of IGBT



Graph.18
Transient thermal resistance of FWD



# ■ Outline Drawings, mm



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